BS EN IEC 61643-341:2020



BSI Standards Publication

Components for low-voltage surge protection

Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)



National foreword

This British Standard is the UK implementation of EN IEC 61643-341:2020. It is identical to IEC 61643-341:2020. It supersedes BS EN 61643-341:2001, which is withdrawn.

The UK participation in its preparation was entrusted to Technical Committee PEL/37/1, Surge Arresters - Low Voltage.

A list of organizations represented on this committee can be obtained on request to its committee manager.

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ISBN 978 0 580 93040 9

ICS 31.080.10; 31.080.20; 29.120.50

Compliance with a British Standard cannot confer immunity from legal obligations.

This British Standard was published under the authority of the Standards Policy and Strategy Committee on 31 July 2020.

Amendments/corrigenda issued since publication

Date

Text affected

EUROPEAN STANDARD

NORME EUROPÉENNE

EUROPÄISCHE NORM

July 2020

EN IEC 61643-341

ICS 31.080.10

Supersedes EN 61643-341:2001 and all of its amendments and corrigenda (if any)

English Version

Components for low-voltage surge protection - Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS) (IEC 61643-341:2020)

Composants pour parafoudres basse tension - Partie 341: Exigences de performance et circuits d'essai pour parafoudres à thyristor (TSS) (IEC 61643-341:2020) Bauelemente für Überspannungsschutzgeräte für Niederspannung - Teil 341: Leistungsanforderungen sowie Prüfschaltungen für Suppressordioden (TSS) (IEC 61643-341:2020)

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CEN-CENELEC Management Centre: Rue de la Science 23, B-1040 Brussels

European foreword

The text of document 37B/218/FDIS, future edition 2 of IEC 61643-341, prepared by SC 37B "Components for low-voltage surge protection" of IEC/TC 37 "Surge arresters" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 61643-341:2020.

The following dates are fixed:

- latest date by which the document has to be implemented at national (dop) 2021-03-17 level by publication of an identical national standard or by endorsement
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In the official version, for Bibliography, the following notes have to be added for the standards indicated:

IEC 60060-1:2010	NOTE	Harmonized as EN 60060-1:2010 (not modified)
IEC 60068-2-20:2008	NOTE	Harmonized as EN 60068-2-20:2008 (not modified)
IEC 60068-2-21:2006	NOTE	Harmonized as EN 60068-2-21:2006 (not modified)
IEC 60099-4:2014	NOTE	Harmonized as EN 60099-4:2014 (not modified)
IEC 60721-3-3:2019	NOTE	Harmonized as EN IEC 60721-3-3:2019 (not modified)
IEC 60721-3-9:1993	NOTE	Harmonized as EN 60721-3-9:1993 (not modified)
IEC 60749-1:2002	NOTE	Harmonized as EN 60749-1:2003 (not modified)
IEC 60950-1:2005	NOTE	Harmonized as EN 60950-1:2006 (modified)
IEC 61000-4-5:2014	NOTE	Harmonized as EN 61000-4-5:2014 (not modified)
IEC 61643-11:2011	NOTE	Harmonized as EN 61643-11:2012 (modified)
IEC 62475:2010	NOTE	Harmonized as EN 62475:2010 (not modified)

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

COMPONENTS FOR LOW-VOLTAGE SURGE PROTECTION -

Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)

FOREWORD

- 1) The International Electrotechnical Commission (IEC) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of IEC is to promote international co-operation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, IEC publishes International Standards, Technical Specifications, Technical Reports, Publicly Available Specifications (PAS) and Guides (hereafter referred to as "IEC Publication(s)"). Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
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International Standard IEC 61643-341 has been prepared by subcommittee 37B, Components for low-voltage surge protection, of IEC technical committee 37: Surge arresters.

This second edition of IEC 61643-341 cancels and replaces the first edition published in 2001. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition: Addition of performance values.

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The text of this standard is based on the following documents:

FDIS	Report on voting
37B/218/FDIS	37B/220/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts of IEC 61643 series, under the general title *Components for low-voltage surge protective devices*, can be found on the IEC website.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed;
- withdrawn;
- replaced by a revised edition, or
- amended.

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COMPONENTS FOR LOW-VOLTAGE SURGE PROTECTION -

Part 341: Performance requirements and test circuits for thyristor surge suppressors (TSS)

1 Scope

This part of IEC 61643 specifies standard test circuits and methods for thyristor surge suppressor (TSS) components. These surge protective components, SPCs, are specially formulated thyristors designed to limit overvoltages and divert surge currents by clamping and switching actions. These SPCs are used in the construction of surge protective devices (SPDs) and equipment used in Information & Communications Technologies (ICT) networks with voltages up to AC 1 000 V and DC 1 500 V. This document is applicable to gated or non-gated TSS components with third quadrant (-v and -i) characteristics of blocking, conducting or switching.

This document contains information on

- terminology;
- letter symbols;
- essential ratings and characteristics;
- rating verification and characteristic measurement;

This document does not apply to the conventional three-terminal thyristors as covered by IEC 60747-6.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60050-521, International Electrotechnical Vocabulary – Chapter 521: Semiconductor devices and integrated circuits

IEC 60068-2-20:2008, Environmental testing – Part 2-20: Tests – Test T: Test methods for solderability and resistance to soldering heat of devices with leads

3 Terms, definitions, abbreviated terms and symbols

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at http://www.electropedia.org/
- ISO Online browsing platform: available at http://www.iso.org/obp